

isc Silicon PNP Power Transistor
2SB649A
ELECTRICAL CHARACTERISTICS

 T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA ; I _E = 0	-180			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA ; R _{BE} = ∞	-160			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA ; I _C =0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -500mA ; I _B = -50mA			-1.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -150mA ; V _{CE} = -5V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -160V ; I _E = 0			-10	μ A
h _{FE-1}	DC Current Gain	I _C = -150mA ; V _{CE} = -5V	60		200	
h _{FE-2}	DC Current Gain	I _C =-500mA ; V _{CE} = -5V	30			
f _T	Current-Gain—Bandwidth Product	I _C = -150mA ; V _{CE} = -5V		140		MHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = -10V, f _{test} = 1MHz		27		pF

◆ h_{FE-1} Classifications

B	C
60-120	100-200